REMARKS

Reconsideration and allowance of the above-amended application are respectfully requested. Claims 44, 72, 78, 84, 90, 95, and 100 have been amended. Each amendment is supported by the original specification. No new matter is added.

Attached is a marked-up version of the changes being made by the current amendment. Claims 44-48, 51-54, 70, and 72-104 remain pending.

Claims 44-48, 51-54, 70, and 72-83, 90-91, 93-96, and 98-99 stand rejected under 35 USC 103(a) as being obvious over Mawatari in view of USPN 5,821,559 to Yamazaki. These claims as amended, however, are patentable over the alleged combination of Mawatari and Yamazaki.

Each independent claim has been amended to recite a resin formed on the substrate, a base film in contact with the resin, and a driver circuit comprising thin film transistors on the base film. This recited structure is fully supported by the original specification, e.g., the embodiment shown in FIG. 7B and the related textual description on page 10.

In contrast, as correctly stated by the Office Action,
Mawatari's driver circuit 120 with TFTs is formed on the
substrate 118a and is secured to the glass substrate 101 by the

resin 125 filled between the elements and the glass substrate 101 (FIGS. 3-5, and Col. 6, lines 65-68). This structure in Mawatari is entirely different from the structures in the pending claims for several reasons. For example, Mawatari fails to teach that the recited base film is in contact with the recited resin in the pending claims. In addition, Mawatari fails to teach that the recited driver circuit is on the base film. In fact, the driver circuit in Mawatari is formed on a different substrate 118a and the whole driver on the substrate 118a is then adhered to the substrate 101 with the resin 125. The driver circuit of the pending claims, however, is formed on the same substrate where the display TFT pixels are formed.

Yamasaki does not fill these voids in the disclosure of Mawatari. Hence, the alleged combination of Mawatari and Yamasaki does not disclose each and every feature recited in the pending claims. Under 35 USC 103(a), the pending claims as amended are distinctly different from, and thus are patentable over, Mawatari in view of Yamasaki.

Like Yamasaki, Sawatsubashi further fails to fill the void left by Mawatari. Therefore, Claim 48 is patentable over the combined teaching of Mawatari, Yamasaki, and Sawatsubashi.

Hence, all pending claims as amended above are distinctly patentable under 35 USC 103(a) over the cited prior art references.

As for the rejections based on obviousness-type double patenting over USPN. 5,834,327, Applicant disagrees for a number of reasons. For example, Claims 5 and 17 of USPN. 5,834,327 do not recite the resin or the base film formed in contact with the resin. Hence, the pending claims of this application are distinctly different from Claims 5 and 17 of USPN. 5,834,327 and the rejections should be withdrawn.

In view of the above, Applicant asks that all claims be allowed and the rejections be withdrawn. Please apply the one month extension of time fee in the amount of \$110, and any other applicable charges or credits, to Deposit Account No. 06-1050.

Respectfully submitted,

Date: November 19, 2002

Req. No. 43,312

PTO Customer No. 20985

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Version with markings to show changes made

In the claims:

a substrate;

Claims 44, 72, 78, 84, 90, 95, and 100 have been amended as follows:

- 44. An active matrix type display device comprising:
- a pixel circuit formed over said substrate for switching pixels of said display device;
 - a resin formed on said substrate;
 - a base film in contact with said resin;
- a driver circuit comprising thin film transistors

 [adhered to said substrate by a resin] on said base film, each of said thin film transistors comprising a semiconductor layer and a gate electrode with a gate insulating film interposed therebetween;
- a passivation film covering said driver circuit, said passivation film having a contact hole to allow an electrical connection between at least one of said thin film transistors and said pixel circuit;
- a wiring formed over said passivation film to form said electrical connection; and

a sealing member over said substrate, wherein said sealing member encloses said pixel circuit and said driver circuit.

72. An active matrix type display device comprising:

a pixel circuit formed over a substrate for switching
pixels of said display device;

a resin formed on said substrate;

a base film in contact with said resin;

a driver circuit comprising thin film transistors

[adhered to said substrate by a resin] on said base film, each of said thin film transistors comprising a semiconductor layer and a gate electrode with a gate insulating film interposed therebetween;

an insulating film formed over said driver circuit; and

a wiring formed over said insulating film, wherein said driver circuit is electrically connected to said pixel circuit through said wiring.

78. An active matrix type display device comprising:

a pixel circuit formed over a substrate for switching
pixels of said display device;

- a resin formed on said substrate;
- a base film in contact with said resin;

a driver circuit comprising thin film transistors

[adhered to said substrate by a resin] on said base film, each of said thin film transistors comprising a semiconductor layer and a gate electrode with a gate insulating film interposed therebetween;

an insulating film formed over said driver circuit; and

a wiring comprising indium tin oxide formed over said insulating film, wherein said driver circuit is electrically connected to said pixel circuit through said wiring.

- 84. An active matrix type display device comprising:

 a pixel circuit formed over a substrate for switching
 pixels of said display device;
 - a resin formed on said substrate;
 - a base film in contact with said resin;
- a driver circuit comprising thin film transistors

 [adhered to said substrate by a resin] on said base film, each of said thin film transistors comprising a semiconductor layer and a gate electrode with a gate insulating film interposed therebetween;

an insulating film formed over said driver circuit; and

a wiring comprising indium tin oxide formed over said insulating film and extending on a same layer as said resin, wherein said driver circuit is electrically connected to said pixel circuit through said wiring.

- 90. An active matrix type display device comprising:
- a pixel circuit formed over a substrate for switching pixels of said display device;
 - a resin formed over said substrate;
 - a base film [on] in contact with said resin;
 - a semiconductor layer on said base film;
- a gate electrode over said semiconductor layer with a gate insulating film interposed therebetween;
- at least one of source and drain electrodes electrically connected to said semiconductor layer;
- an insulating film formed over at least said semiconductor layer and said gate electrode; and
- a wiring formed over said insulating film, wherein said at least one of said source and drain electrodes is electrically connected to said pixel circuit through said wiring.

- 95. An active matrix type display device comprising:
- a pixel circuit formed over a substrate for switching pixels of said display device;
 - a resin formed over said substrate;
 - a base film [on] in contact with said resin;
 - a semiconductor layer on said base film;
- a gate electrode over said semiconductor layer with a gate insulating film interposed therebetween;
- at least one of source and drain electrodes electrically connected to said semiconductor layer;
- an insulating film formed over at least said semiconductor layer and said gate electrode; and
- a wiring comprising indium tin oxide formed over said insulating film, wherein said at least one of said source and drain electrodes is electrically connected to said pixel circuit through said wiring.
 - 100. An active matrix type display device comprising:
- a pixel circuit formed over a substrate for switching pixels of said display device;
 - a resin formed over said substrate;
 - a base film [on] in contact with said resin;

a semiconductor layer on said base film;

a gate electrode over said semiconductor layer with a gate insulating film interposed therebetween;

at least one of source and drain electrodes electrically connected to said semiconductor layer;

an insulating film formed over at least said semiconductor layer and said gate electrode; and

a wiring comprising indium tin oxide formed over said insulating film and extending on a same layer as said resin, wherein said at least one of said source and drain electrodes is electrically connected to said pixel circuit through said wiring.